



### P-Channel Enhancement Mode Power MOSFET

- **Features**

$V_{DS} = -20V$

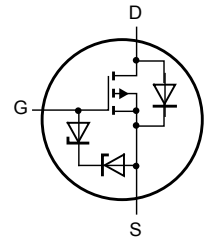
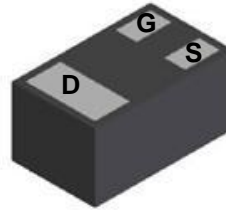
$I_D = -0.5A$

$R_{DS(ON)} \leq 345m\Omega (V_{GS} = -4.5V)$

- **General Description**

The TPM04K20BX is P-Channel enhancement MOSFET Transistor. Uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$ , with low gate charge. This device is suitable for use in DC-DC conversion, power switch and charging circuit.

- **Pin Configurations**



- **Package Information**

**P-Channel Enhancement Mode Power MOSFET**
**● Absolute Maximum Ratings (@TA=25°C unless otherwise noted)**

Parameter	Symbol	Ratings	Unit	
Drain-Source Voltage	$V_{DSS}$	-20	V	
Gate Source Voltage	$V_{GSS}$	±8	V	
Drain Current (Continuous) *AC	$I_D$	$T_A=25^\circ\text{C}$	-0.5	A
		$T_A=100^\circ\text{C}$	-0.4	
Drain Current (Pulse) *B	$I_{DM}$	-1.2	A	
Power Dissipation	$P_D$	0.3	W	
Operating Temperature/ Storage Temperature	$T_J/T_{STG}$	-55~155	°C	

**● Thermal Characteristics**

Parameter	Symbol	Ratings	Unit
Thermal Resistance ,Junction-to-Ambient	$R_{\theta JA}$	416	°C/W

**● Electrical Characteristics (@TA=25°C unless otherwise noted)**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-20	--	--	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-20V, V_{GS}=0V$	--	--	-1	uA
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_{DS}=-250\mu A$	-0.4	--	-1.2	V
Gate Leakage Current	$I_{GSS}$	$V_{GS}=\pm 8V, V_{DS}=0V$	--	--	±10	uA
Drain-Source On-state Resistance	$R_{DS(on)}$	$V_{GS}=-4.5V, I_D=-0.3A$	--	--	345	mΩ
		$V_{GS}=-2.5V, I_D=-0.3A$	--	--	555	mΩ
Total Gate Charge	$Q_g$	$V_{GS}=-4.5V, V_{DS}=-10V, I_D=-0.45A$	--	0.9	--	nC
Gate- Source Charge	$Q_{gs}$		--	0.16	--	nC
Gate- Drain Charge	$Q_{gd}$		--	0.27	--	nC
Turn-on Delay Time	$t_{d(on)}$	$V_{GS}=-4.5V, V_{DS}=-10V, R_{GEN}=6\Omega, I_D=-0.45A$	--	45	--	ns
Turn-on Rise Time	$t_r$		--	140	--	ns
Turn-off Delay Time	$t_{d(off)}$		--	1500	--	ns
Turn-off Fall Time	$t_f$		--	2100	--	ns
Input Capacitance	$C_{iss}$	$V_{GS}=0V, V_{DS}=-10V, f=1\text{MHZ}$	--	74.5	--	pF
Output Capacitance	$C_{oss}$		--	10.8	--	pF
Reverse Transfer Capacitance	$C_{rss}$		--	10.2	--	pF

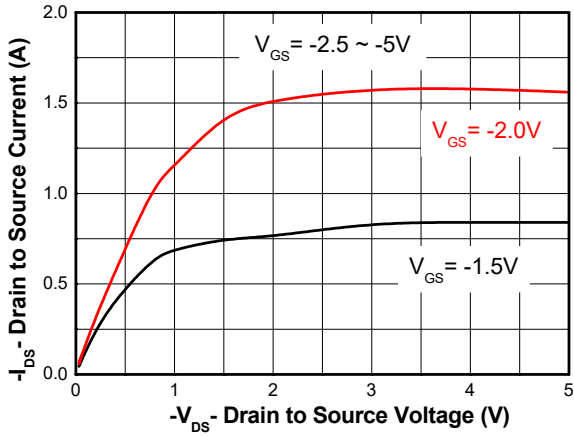
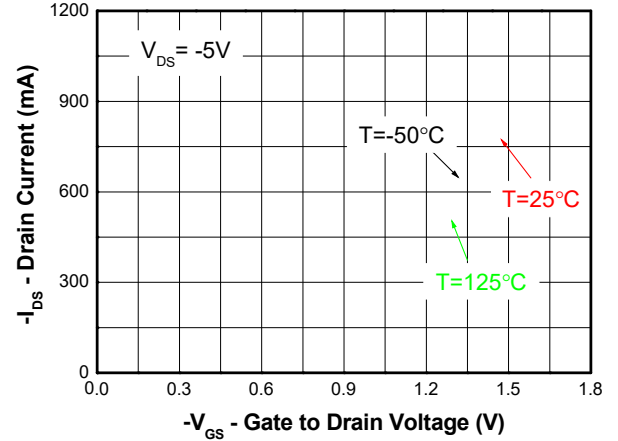
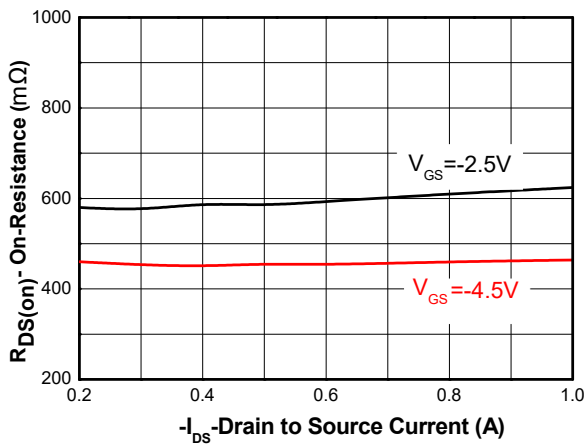
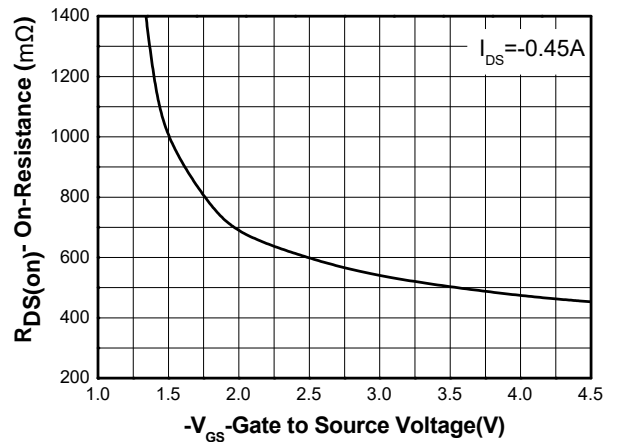
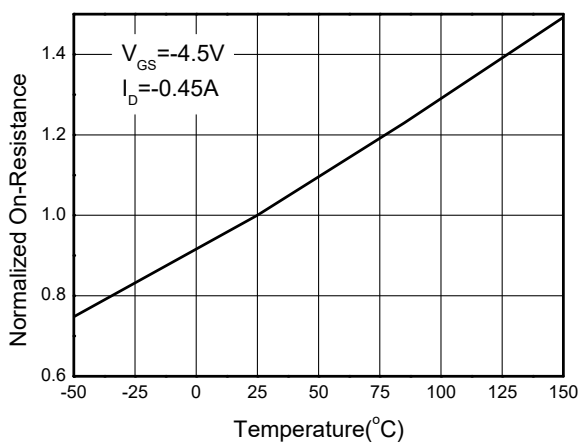
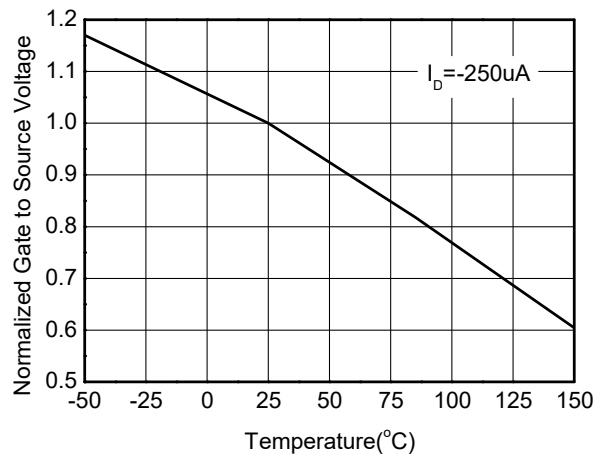
**P-Channel Enhancement Mode Power MOSFET****● Reverse Diode Characteristics (@TA=25°C unless otherwise noted)**

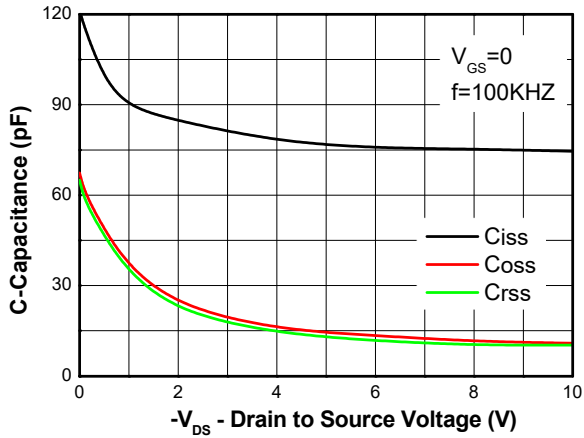
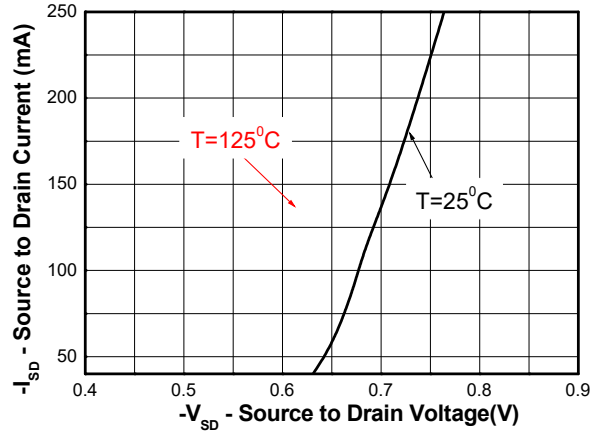
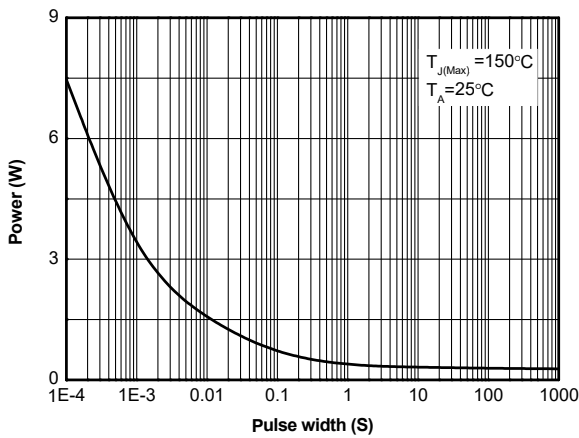
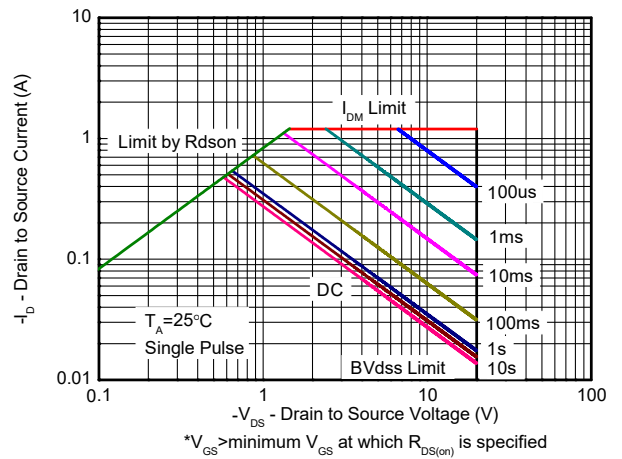
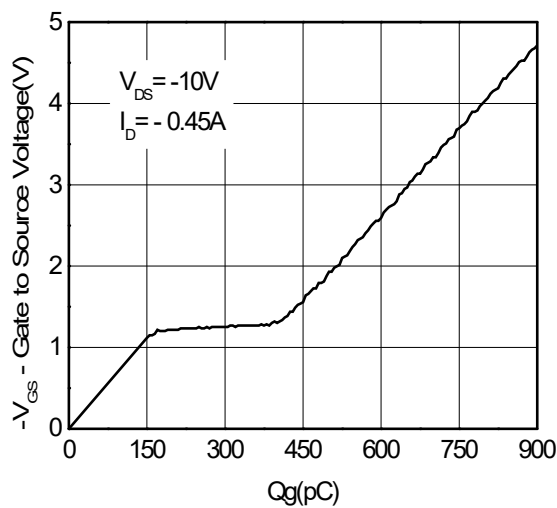
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Continuous Diode Forward Current	$I_{SD}$	$V_G=V_D=0V$ , Force Current	--	--	-0.5	A
Diode Forward Voltage	$V_{SD}$	$I_{SD}=-0.5A$ , $V_{GS}=0V$	--	--	-1.2	V

A: The value of  $R_{\theta JA}$  is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25C$ . The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature .

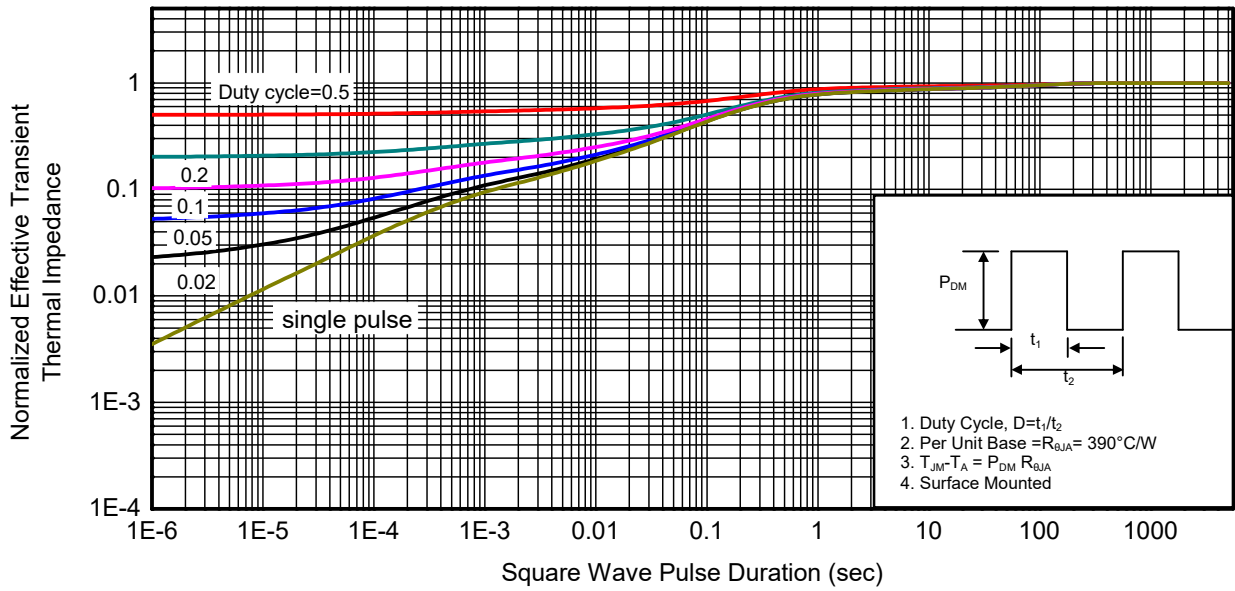
C: The current rating is based on the  $t < 10s$  junction to ambient thermal resistance rating.

**P-Channel Enhancement Mode Power MOSFET**
**● TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**

**Output characteristics**

**Transfer characteristics**

**On-Resistance vs. Drain current**

**On-Resistance vs. Gate-to-Source voltage**

**On-Resistance vs. Junction temperature**

**Threshold voltage vs. Temperature**

**P-Channel Enhancement Mode Power MOSFET**

**Capacitance**

**Body diode forward voltage**

**Single pulse power**

**Safe operating power**




### P-Channel Enhancement Mode Power MOSFET



Transient thermal response (Junction-to-Ambient)

## X-ON Electronics

Largest Supplier of Electrical and Electronic Components

*Click to view similar products for [MOSFET](#) category:*

*Click to view products by [Shenzhen JingYang](#) manufacturer:*

Other Similar products are found below :

[IRFD120](#) [JANTX2N5237](#) [BUK455-60A/B](#) [MIC4420CM-TR](#) [VN1206L](#) [NDP4060](#) [SI4482DY](#) [IPS70R2K0CEAKMA1](#) [SQD23N06-31L-GE3](#)  
[TK16J60W,S1VQ\(O](#) [2SK2614\(TE16L1,Q\)](#) [DMN1017UCP3-7](#) [DMN1053UCP4-7](#) [SQJ469EP-T1-GE3](#) [NTE2384](#) [DMC2700UDMQ-7](#)  
[DMN2080UCB4-7](#) [DMN61D9UWQ-13](#) [US6M2GTR](#) [DMN31D5UDJ-7](#) [DMP22D4UFO-7B](#) [DMN1006UCA6-7](#) [DMN16M9UCA6-7](#)  
[STF5N65M6](#) [IRF40H233XTMA1](#) [STU5N65M6](#) [DMN6022SSD-13](#) [DMN13M9UCA6-7](#) [DMTH10H4M6SPS-13](#) [DMN2990UFB-7B](#)  
[IPB80P04P405ATMA2](#) [2N7002W-G](#) [MCAC30N06Y-TP](#) [MCQ7328-TP](#) [NTMC083NP10M5L](#) [NVMFS2D3P04M8LT1G](#) [BXP7N65D](#)  
[BXP4N65F](#) [AOL1454G](#) [WMJ80N60C4](#) [BXP2N20L](#) [BXP2N65D](#) [BXT1150N10J](#) [BXT1700P06M](#) [TSM60NB380CP](#) [ROG](#) [RQ7L055BGTCR](#)  
[DMNH15H110SK3-13](#) [SLF10N65ABV2](#) [BSO203SP](#) [BSO211P](#)